

ABSTRACT OF THE DISCLOSURE

To provide a manufacturing method for a semiconductor device, with which it is possible to prevent silicon oxynitride formed upon nitriding a first gate oxide film from inhibiting oxidation of a second gate oxide film to keep a high reliability of the second gate oxide film. When a first gate insulating film is removed for forming the second gate oxide film or when a silicon substrate is washed just before the formation of the second gate oxide film, treatment with an ammonia-hydrogen peroxide solution is added, whereby a silicon oxynitride film at a site where the second gate oxide film is formed can be removed prior to the formation of the second gate oxide film.